

CentralTM Semiconductor Corp.

145 Adams Ave., Hauppauge, NY 11788 USA
Phone (516) 435-1110 FAX (516) 435-1824

Manufacturers of World Class Discrete Semiconductors

CMPFJ310

SURFACE MOUNT
SILICON N-CHANNEL JFET

SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPFJ310 type is a epoxy molded N-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for VHF/UHF amplifier applications.

Marking code is 6T.

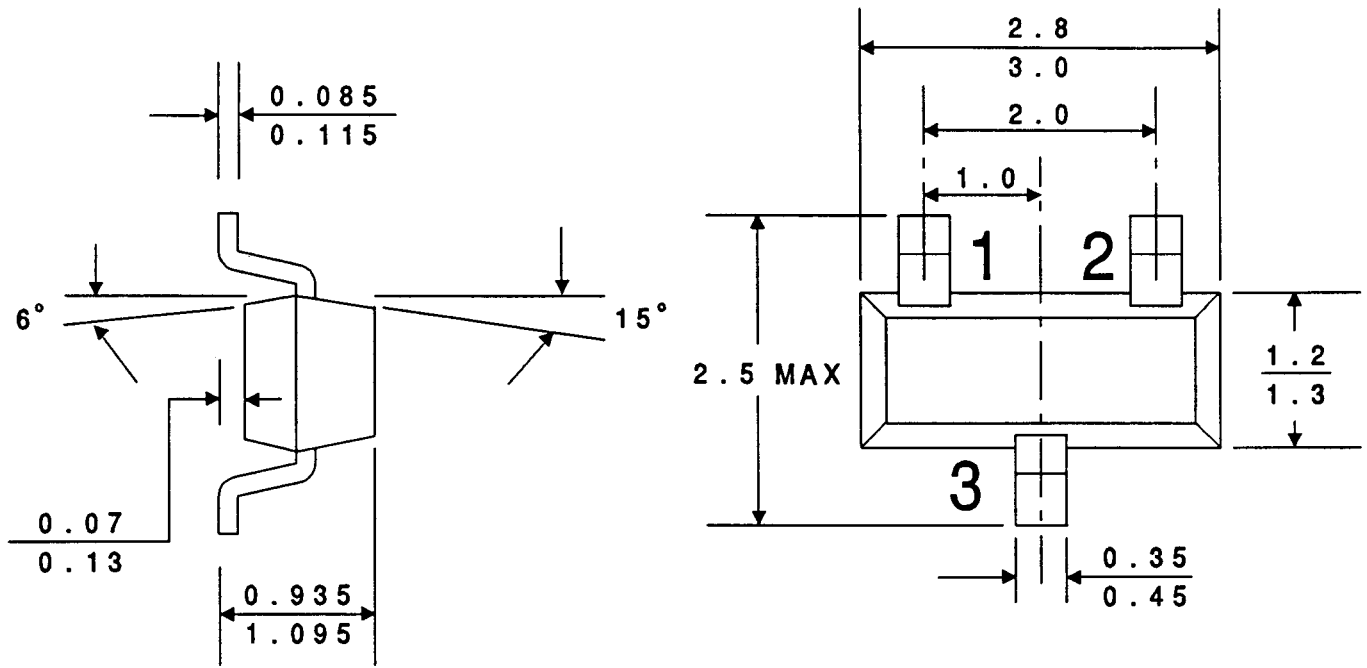
MAXIMUM RATINGS (T_A = 25°C)

	SYMBOL		UNITS
Drain-Source Voltage	V _{DS}	25	V
Gate-Source Voltage	V _{GS}	25	V
Gate Current	I _G	10	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{GSS}	V _{GS} = 15V			1.0	nA
I _{GSS}	V _{GS} = 15V, T _A = 125°C			1.0	μA
I _{DSS}	V _{DS} = 10V, V _{GS} = 0	24		60	mA
BV _{GSS}	I _G = 1.0μA	25			V
V _{GS(off)}	V _{DS} = 10V, I _D = 1.0nA	2.0		6.5	V
V _{GS(f)}	I _G = 1.0mA, V _{DS} = 0			1.0	V
Y _{fs}	V _{DS} = 10V, I _D = 10mA, f = 1.0kHz	8.0		18	mmhos
Y _{os}	V _{DS} = 10V, I _D = 10mA, f = 1.0kHz			250	μmhos
C _{iss}	V _{GS} = 10V, V _{DS} = 0, f = 1.0MHz			5.0	pF
C _{rss}	V _{GS} = 10V, V _{DS} = 0, f = 1.0MHz			2.5	pF
\bar{e}_n	V _{DS} = 10V, I _D = 10mA, f = 100Hz		10		nV/√Hz

All Dimensions in mm.



LEAD CODE:

MARKING CODE: 6T

- 1) SOURCE
- 2) DRAIN
- 3) GATE